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emid. a sidewall diffusion barrier layer disposed on sidewalls of said via, said sidewall diffusion barrier layer formed by reverse sputtering of said first diffusion barrier layer, wherein said sidewall diffusion barrier and said sidewall diffusion barrier layer are formed from a same material.

3. (Amended) The semiconductor device according to claim 4, wherein said second etch stop layer includes silicon oxide

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Sub B2
4. (Amended) A semiconductor device, comprising:
a first metallization layer;
a first diffusion barrier layer disposed over said first metallization layer;
a second etch stop layer disposed on and contacting said first metallization layer;
a first etch stop layer disposed on and contacting said second etch stop layer;
a dielectric layer disposed on and contacting said first etch stop layer;
a via extending through said dielectric layer, said first etch stop layer, said second etch stop layer and said first diffusion barrier layer, wherein said second etch stop layer has a thickness of at least 50 angstroms to about 120 angstroms.

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5. (Amended) The semiconductor device according to claim 1, wherein said material of said first diffusion barrier layer includes silicon nitride.

A4
6. (Amended) The semiconductor device according to claim 1, further comprising a second diffusion barrier layer disposed over said sidewall diffusion barrier layer.